

OptiMOS™ and StrongIRFET™ combined portfolio

20 V-300 V N-channel Power MOSFETs



A powerful combination

Infineon's semiconductors are designed to bring more efficiency, power density and cost effectiveness. The full range of OptiMOS™ and StrongIRFET™ N-channel Power MOSFETs enable innovation and performance in applications such as switch mode power supplies (SMPS), motor control and drives, inverters and computing.

Power MOSFETs 20 V-300 V - OptiMOS™ and StrongIRFET™ families

Infineon's highly innovative OptiMOS[™] and StrongIRFET[™] families consistently meet the highest quality and performance demands in key specifications for power system design such as on-state resistance and figure of merit characteristics. OptiMOS[™] is the market leader in highly efficient solutions for power generation (e.g. solar micro inverter), power supply (e.g. server and telecom) and power consumption (e.g. electric vehicle).

OptiMOS™ – optimized for high frequency and low R_{DS(on)} applications



Benefits

- > Expanded product portfolio 20 V-300 V
- > Able to address a broad range of needs
- > Best-in-class technology → OptiMOS[™]

StrongIRFET™ – optimized for low frequency and high rugged applications



Family attributes overview

OptiMOS™ Power MOSFETs provide excellent best-in-class performance. Features include ultra low R_{DS(on)} as well as low charge for high switching frequency applications. StrongIRFET™ Power MOSFETs are designed for rugged industrial applications and are ideal for designs with a low switching frequency as well as those that require a high current carrying capability.

OptiMOS™ family attributes

Designed for high performance applications

performance products

Designed for industrial applications

StrongIRFET™ family attributes

Primarily aimed at replacing planar Power MOSFETs

Provide value in traditional Trench MOSFET space

Ideal for high switching frequency

Ultra low R_{DS(on)}

199

20 V-300 V portfolio

Primarily aimed at replacing

Trench Power MOSFETs

Industry best figure of merit

High efficiency and power density

Ideal for low switching frequency

Low R_{DS(on)}

3.0 Threshold voltage

Logic Level also available

Rugged Silicon

High current carrying capability

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Product family positioning

These graphs show the recommended technology for best fit standard components, price performance and differentiated products according to switching frequency.

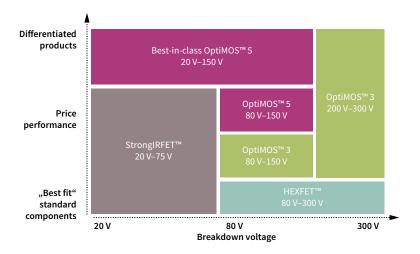
For low frequency applications, OptiMOS™ 5 is the best fit when best-in-class performance is required. However, StrongIRFET™ is recommended for 20 V to 75 V applications when best-in-class performance is not essential and cost is a more significant consideration.

For best-in-class performance at voltages from 80 V to 150 V, OptiMOS™ 5 is recommended. If best-in-class is not essential and price/performance is more important, then OptiMOS™ 3 is the recommendation.

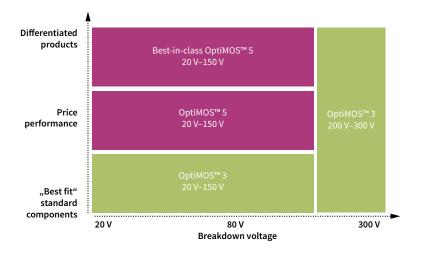
Voltages above 150 V are available in OptiMOS™ 3. In addition, older Trench MOSFETs, shown here as HEXFET™, are an option for highly commoditized markets where cost is the main consideration.

For high frequency applications, OptiMOS™ 5 is recommended for best-in-class and price/performance up to 150 V. OptiMOS™ 3 can be considered where high performance is less essential. As with low frequency applications, OptiMOS™ 3 is available for voltages above 150 V.

Low frequency applications < 100 kHz



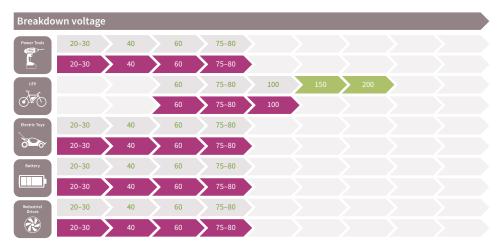
High frequency applications > 100 kHz



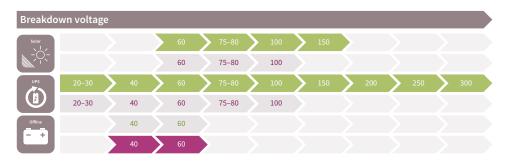
Combined portfolio

Infineon's OptiMOS[™] portfolio, now complemented by StrongIRFET[™] Power MOSFETs, creates a truly powerful combination. The joint portfolio, covering 20 V up to 300 V MOSFETs, can address a broad range of needs from low to high switching frequencies. The tables below provide a guidance overview for the recommended OptiMOS[™] or StrongIRFET[™] products for each major sub-application and voltage class.

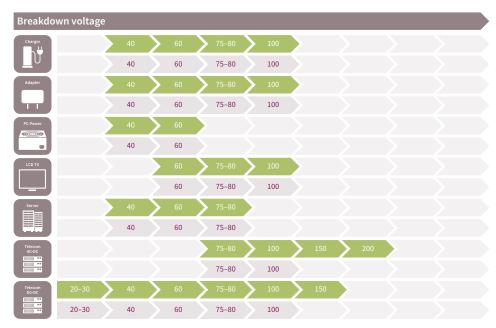
Drives



Inverters



SMPS



Legend



Packages available by voltage class

